

U.S. PTO
12/589045
10/16/2009

Form PTO-1595 (Rev. 12-08)
OMB No. 0651-0027 (exp. 01/31/2009)

U.S. DEPARTMENT OF COMMERCE
United States Patent and Trademark Office

10-28-2009



103578897

ET

To the Director of the U.S. Patent a

documents or the new address(es) below.

1. Name of conveying party(ies)

Sung-Shan Tai, Yong-Zhong Hu, Francois Hebert
Hong Chang, Mengyu Pan, Yingying Lou, Yu Wang

Additional name(s) of conveying party(ies) attached? ☐ Yes ☒ No

3. Nature of conveyance/Execution Date(s):

Execution Date(s) December 19, 2006

- ☒ Assignment ☐ Merger
☐ Security Agreement ☐ Change of Name
☐ Joint Research Agreement
☐ Government Interest Assignment
☐ Executive Order 9424, Confirmatory License
☐ Other _____

2. Name and address of receiving party(ies)

Name: Alpha & Omega Semiconductor, LTD

Internal Address: _____

Street Address: Cannon's Court 22, Victoria Street

City: Hamilton HM12

State: _____

Country: BERMUDA

Zip: _____

Additional name(s) & address(es) attached? ☐ Yes ☒ No

4. Application or patent number(s):

☒ This document is being filed together with a new application.

A. Patent Application No.(s)

B. Patent No.(s)

Additional numbers attached? ☐ Yes ☒ No

5. Name and address to whom correspondence concerning document should be mailed:

Name: Bo-In Lin

Internal Address: _____

Street Address: 13445 Mandoli Drive

City: Los Altos Hills

State: CA Zip: 94022

Phone Number: 650-949-0418

Fax Number: 650-949-4118

Email Address: BoInlin@aol.com

6. Total number of applications and patents involved: 1

7. Total fee (37 CFR 1.21(h) & 3.41) \$ 40

- ☐ Authorized to be charged to deposit account
☒ Enclosed - on PTO-2038 form
☐ None required (government interest not affecting title)

8. Payment Information

Deposit Account Number _____

Authorized User Name _____

9. Signature:

Signature

2009-10-16
Date

Bo-In Lin

Name of Person Signing

Total number of pages including cover sheet, attachments, and documents: ☐

Documents to be recorded (including cover sheet) should be faxed to (571) 273-0140, or mailed to:
Mail Stop Assignment Recordation Services, Director of the USPTO, P.O.Box 1450, Alexandria, V.A. 22313-1450

10/20/2009 CNGUYEN2 00000044 12589045

01 FC:8021

40.00 DP

PATENT
REEL: 023433 FRAME: 0645

ASSIGNMENT

INVENTOR
AND CITY

Whereas, I, **Sung-Shan Tai** of 1256 Lockhaven Way,
San Jose, California 95129

have invented:

TITLE:

**SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYER**

DATE INVENTOR
SIGNED THE
DECLARATION

and executed a United States patent application therefor

on Dec. 18th, 2006;

Whereas, **Alpha & Omega Semiconductor, LTD**, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called **AOS**), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to **AOS**, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to **AOS** its successors and assigns; and I hereby agree that **AOS** may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

Signed and Sealed at Sunnyvale, California

DATE

on Dec. 18th, 2006.



SIGNATURE OF INVENTOR

ASSIGNMENT

INVENTOR
AND CITY

Whereas, I, Yong-Zhong Hu of 7584 Peach Blossom Drive
Cupertino, CA 95014

have invented:

TITLE:

SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYER

DATE INVENTOR
SIGNED THE
DECLARATION

and executed a United States patent application therefor

on Dec. 18, 2006;

Whereas, Alpha & Omega Semiconductor, LTD, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

Signed and Sealed at Sunnyvale, California

DATE

on Dec. 18, 2006.


SIGNATURE OF INVENTOR

ASSIGNMENT

INVENTOR
AND CITY

Whereas, I, **François Hebert** of 18 Melrose Court,
San Mateo, California 94402

have invented:

TITLE:

**SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYER**

DATE INVENTOR
SIGNED THE
DECLARATION

and executed a United States patent application therefor
on Dec 19, 2006;

Whereas, **Alpha & Omega Semiconductor, LTD**, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

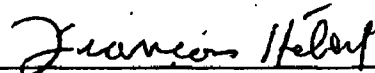
Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

Signed and Sealed at Sunnyvale, California

DATE

on Dec 19, 2006.



SIGNATURE OF INVENTOR

ASSIGNMENT

INVENTOR
AND CITY

Whereas, I, Hong Chang of 11464 Garden Terrace Drive
Cupertino, CA 95014

have invented:

TITLE:

**SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYER**

DATE INVENTOR
SIGNED THE
DECLARATION

and executed a United States patent application therefor
on Dec. 19, 2006;

Whereas, Alpha & Omega Semiconductor, LTD, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

Signed and Sealed at Sunnyvale, California

DATE

on Dec. 19, 2006.


SIGNATURE OF INVENTOR

ASSIGNMENT

INVENTOR Whereas, I, Mengyu Pan of 2nd Floor, Building 18, 498 Guoshoujing Road, Shanghai Pudong Zhangjiang Software Park, Pudaong New Area

AND CITY Shanghai, 201203, PR China

have invented:

TITLE: SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYER

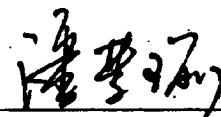
DATE INVENTOR and executed a United States patent application therefor
SIGNED THE
DECLARATION on _____, 2006;

Whereas, Alpha & Omega Semiconductor, LTD, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND Signed and Sealed at Sunnyvale, California

DATE on Dec. 19th, 2006.



SIGNATURE OF INVENTOR

ASSIGNMENT

INVENTOR Whereas, I, Yingying Lou of 2nd Floor, Building 18, 498
Guoshoujing Road, Shanghai Pudong Zhangjiang Software Park,
Pudaong New Area
AND CITY Shanghai, 201203, PR China

have invented:

TITLE: SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYER

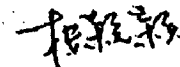
DATE INVENTOR and executed a United States patent application therefor
SIGNED THE
DECLARATION on _____, 2006;

Whereas, Alpha & Omega Semiconductor, LTD, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND Signed and Sealed at Shanghai, PR China

DATE on Dec. 19, 2006.



SIGNATURE OF INVENTOR

ASSIGNMENT

INVENTOR
AND CITYWhereas, I, Yu Wang of 407 Ohlones Street
Fremont, California, Zip 94539

have invented:

TITLE:

SPLIT GATE FORMATION WITH HIGH DENSITY PLASMA (HDP)
OXIDE LAYER AS INTER-POLYSILICON INSULATION LAYERDATE INVENTOR
SIGNED THE
DECLARATION

and executed a United States patent application therefor

on Dec. 19, 2006;

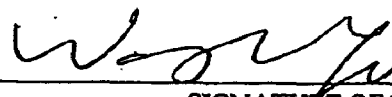
Whereas, Alpha & Omega Semiconductor, LTD, a Bermuda Company, having its registered address at Cannon's Court 22, Victoria Street, Hamilton HM12, Bermuda, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefor;

Now therefore, for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the inventions set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

Signed and Sealed at Fremont, California

DATE

on Dec. 19, 2006.

SIGNATURE OF INVENTOR

PATENT